

IRFR110TRRPBF

IRFR110TRRPBF Information



For Reference Only

Part Number IRFR110TRRPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 4.3A DPAK **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFR110TRRPBF Specifications

Manufacturer Part Number IRFR110TRRPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 4.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 8.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 180pF @ 25V Vgs (Max) E20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 4.3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 180pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds180pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds180pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C4.3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds180pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 8.3nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature Surpface Mount Supplier Device Package Package / Case 4.3A (Tc) 4.2	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs8.3nC @ 10VInput Capacitance (Ciss) (Max) @ Vds180pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) As On (Max) @ Id, Vgs Operating Temperature Found Temperature Supplier Device Package Package / Case 4V @ 250μA 8.3nC @ 10V 180pF @ 25V +20V FET Feature - 2.5W (Ta), 25W (Tc) 540 mOhm @ 2.6A, 10V -55°C ~ 150°C (TJ) Surface Mount TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	4.3A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 180pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 180pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta), 25W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	8.3nC @ 10V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 25W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	180pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 25W (Tc) 8ds On (Max) @ Id, Vgs 540 mOhm @ 2.6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs540 mOhm @ 2.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2.5W (Ta), 25W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	540 mOhm @ 2.6A, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IRFR110TRRPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFR110TRRPBF Payment Methods



















IRFR110TRRPBF Shipping Methods













If you have any question about IRFR110TRRPBF, please do not hesitate to contact us!

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